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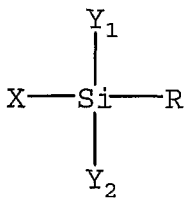
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(54) Title: CAPPING LAYER FORMATION ONTO A DUAL DAMESCENE INTERCONNECT



(Formula I)

(57) Abstract: A process for the formation of a capping layer on a conducting interconnect for a semiconductor device is provided, the process comprising the steps of: (a)providing one or more conductors in a dielectric layer, and (b) depositing a capping layer on an upper surface of at least some of the one or more conductors, characterised in that the process further includes: (c) the step of, prior to depositing the capping layer, reacting the dielectric layer with an organic compound in a liquid phase, the said organic compound having the following general formula: (I) where X is a functional group, R is an organic group or a organosiloxane group, Y1 is either a functional group or an organic group or organosiloxane group, and Y2 is either a functional group or an organic group or organosiloxane group, and where the functional group(s) is / are independently selected from the following: NH2, a secondary amine, a tertiary amine, acetamide, trifluoroacetamide, imidazole, urea, OH, an alkyoxy, acryloxy, acetate, SH, an alkylthiol, sulfonate, methanosulfonate, and cyanide, and salts thereof.